

# XP161A01A8PR



## Power MOS FET

- ◆N-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance:  $0.18\Omega$  (max)
- ◆Ultra High-Speed Switching
- ◆SOT-89 Package

## Applications

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

## General Description

The XP161A01A8PR is an N-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

The small SOT-89 package makes high density mounting possible.

## Features

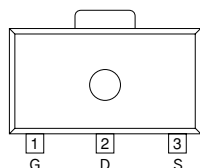
**Low on-state resistance:**  $R_{ds(on)}=0.11\Omega(V_{gs}=10V)$   
:  $R_{ds(on)}=0.18\Omega(V_{gs}=4.5V)$

**Ultra high-speed switching**

**Operational Voltage** : 4.5V

**High density mounting** : SOT-89

## Pin Configuration



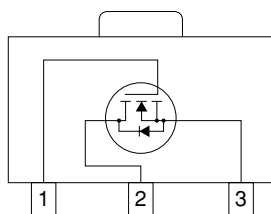
SOT-89  
(TOP VIEW)

## Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	G	Gate
2	D	Drain
3	S	Source

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## Equivalent Circuit



N-Channel MOS FET  
(1 device built-in)

## Absolute Maximum Ratings

$T_a=25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	$V_{ds}$	30	V
Gate-Source Voltage	$V_{gs}$	$\pm 20$	V
Drain Current (DC)	$I_d$	3	A
Drain Current (Pulse)	$I_{dp}$	9	A
Reverse Drain Current	$I_{dr}$	3	A
Continuous Channel Power Dissipation (note)	$P_d$	2	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

Note: When implemented on a ceramic PCB

## Electrical Characteristics

### DC Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds=30V, Vgs=0V			10	μA
Gate-Source Leakage Current	Igss	Vgs=±20V, Vds=0V			±10	μA
Gate-Source Cut-off Voltage	Vgs(off)	Id=1mA, Vds=10V	1.0			V
Drain-Source On-state Resistance (note)	Rds(on)	Id=1.5A, Vgs=10V		0.08	0.11	Ω
		Id=1.5A, Vgs=4.5V		0.14	0.18	Ω
Forward Transfer Admittance (note)	Yfs	Id=1.5A, Vds=10V		3.5		S
Body Drain Diode Forward Voltage	Vf	If=3A, Vgs=0V		0.85	1.1	V

Note: Effective during pulse test.

### Dynamic Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds=10V, Vgs=0V f=1MHz		220		pF
Output Capacitance	Coss			140		pF
Feedback Capacitance	Crss			55		pF

### Switching Characteristics

Ta=25°C

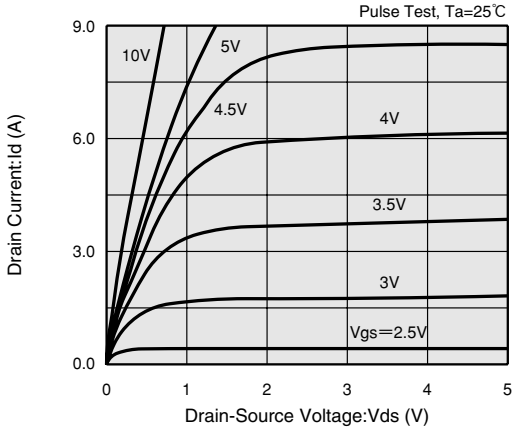
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs=5V, Id=1.5A Vdd=10V		15		ns
Rise Time	tr			15		ns
Turn-off Delay Time	td (off)			25		ns
Fall Time	tf			15		ns

### Thermal Characteristics

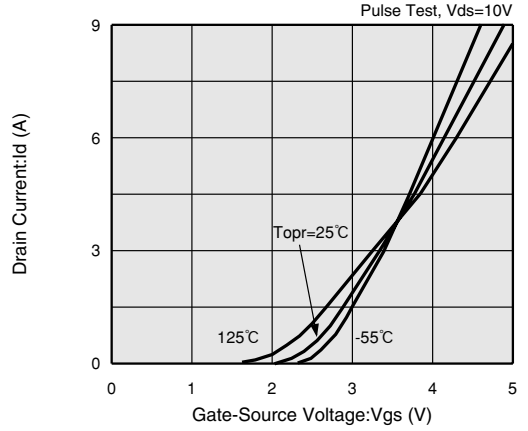
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a ceramic PCB		62.5		°C/W

## Typical Performance Characteristics

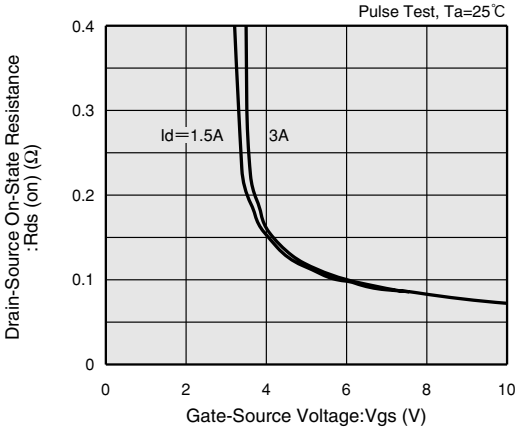
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



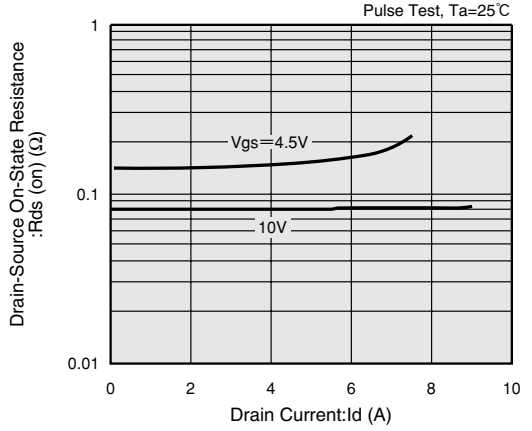
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



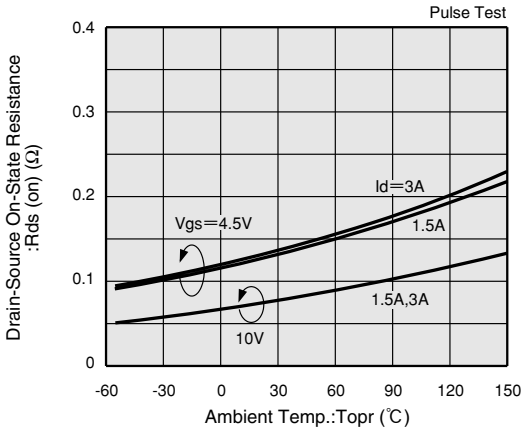
DRAIN-SOURCE ON-STATE RESISTANCE vs. GATE-SOURCE VOLTAGE



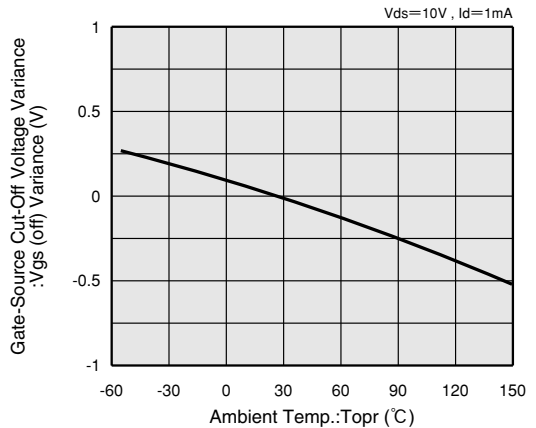
DRAIN-SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



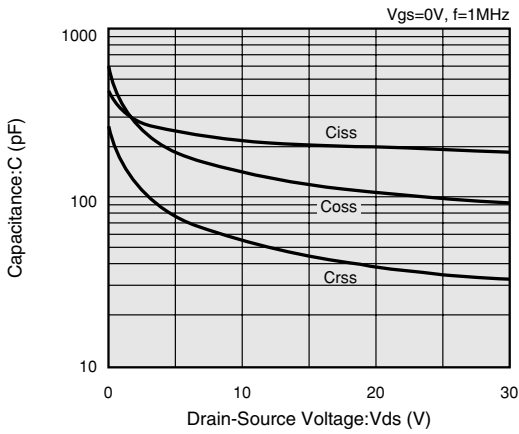
DRAIN-SOURCE ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE



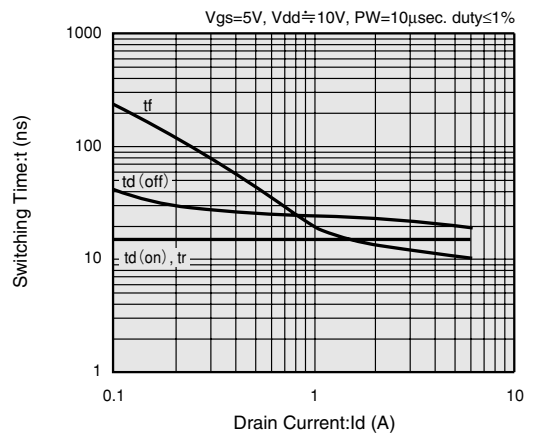
GATE-SOURCE CUT-OFF VOLTAGE VARIANCE vs. AMBIENT TEMPERATURE



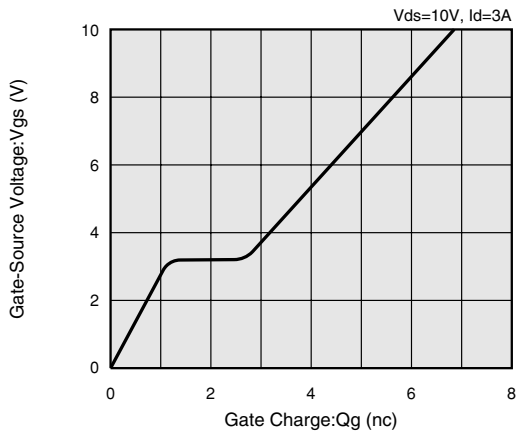
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



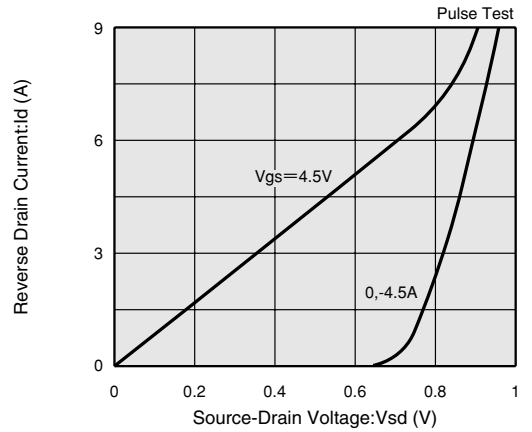
SWITCHING TIME vs. DRAIN CURRENT



GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH

